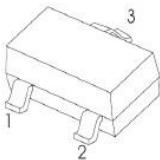




特征 Features

- 开关速度小于 4.0nS;Fast Switching Device (TRR <4.0 nS).
- 最大功率耗散 350mW; Power Dissipation of 350mW.
- 高稳定性和可靠性。High Stability and High Reliability.
- 反向漏电流小。Low reverse leakage



STO-23

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

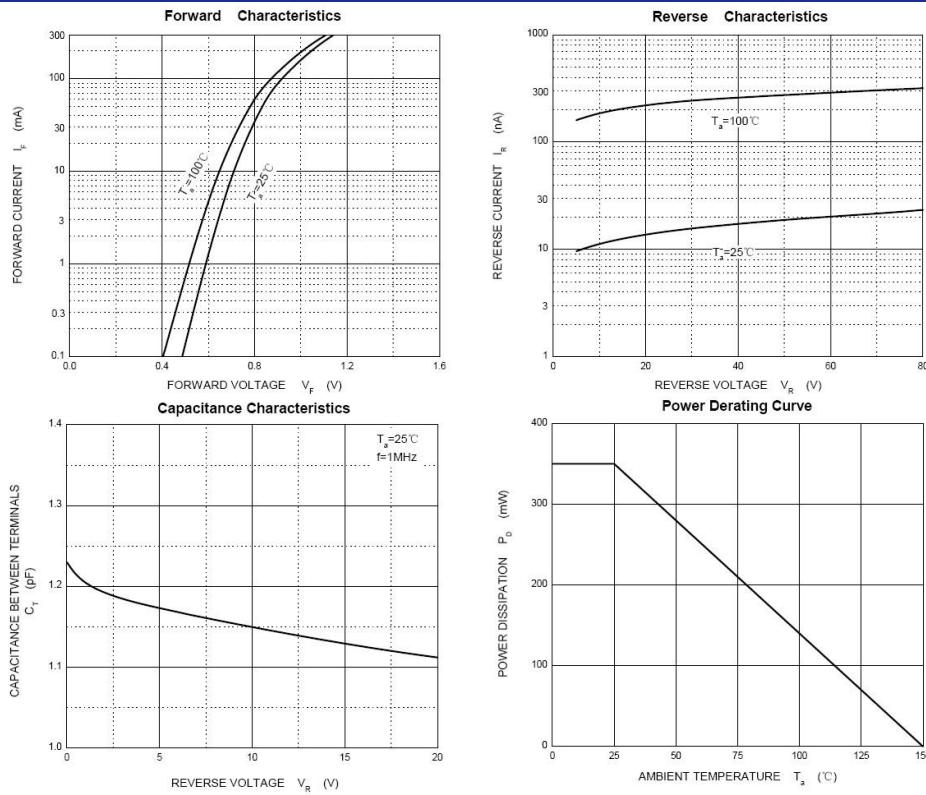
参数 Parameters	符号 Symbol	数值 Value	单位 Unit
反向电压 Reverse Voltage	VR	75	V
反向峰值电压 Peak Repetitive Reverse Voltage	VR _{RRM}	100	V
功率消耗 Power Dissipation	Pd	350	mW
平均整流输出电流 Average Rectified Output Current	I _o	200	mA
正向(不重复)浪涌电流 Non-Repetitive Peak Forward Surge Current @t=8.3ms; TA=25°C	I _{FSM}	2.0	A
工作结温 Operating junction temperature	T _j	150	°C
存储温度 Storage temperature range	T _s	-55~+150	°C
热阻抗 Thermal Resistance from Junction to Ambient	R _{OJA}	357	°C/W

Valid provided that electrodes are kept at ambient temperature.

电特性 Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

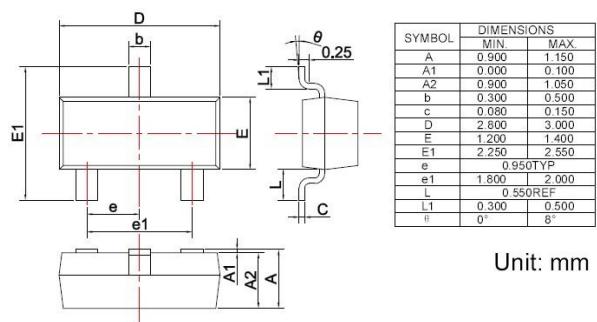
符号 Symbols	参数 Parameter	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
V(BR)	反向电压 Reverse Voltage	I _R =100uA	75		V
I _R	反向漏电电流 Reverse Leakage Current	V _R =75V	---	5.0	uA
		V _R =25V	---	25	uA
V _F	正向电压 Forward Voltage	I _F =10mA	---	1.00	V
TRR	反向恢复时间 Reverse Recovery Time	I _F = I _R =10mA	---	4	nS
		V _R =6V, R _L =100Ω			
		I _{RR} =0.1 X I _R			
CT	结电容 Capacitance	V _R =0V, f=1MHZ	---	4	pF

Typical Characteristics

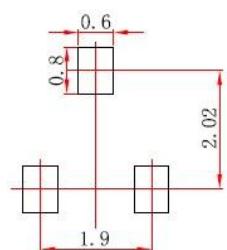


SOT-23 PACKAGE OUTLINE

Plastic surface mounted package



焊盘设计参考 Precautions: PCB Design(Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs)



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.